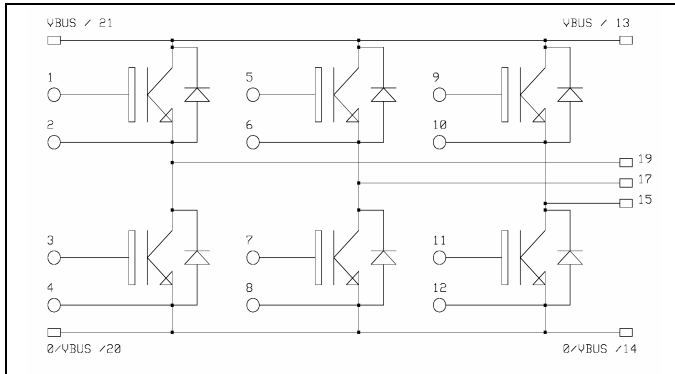


3 Phase bridge NPT IGBT Power Module

**$V_{CES} = 600V$
 $I_C = 150A @ T_c = 80^\circ C$**



Application

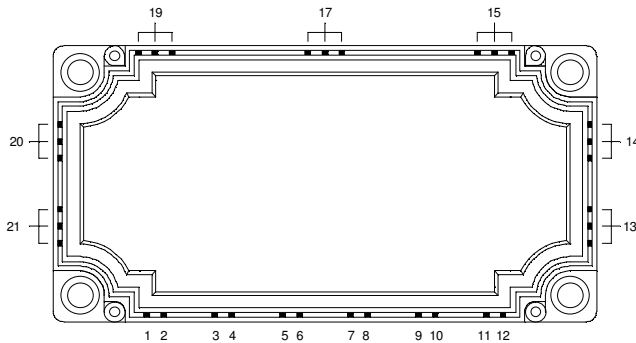
- AC Motor control

Features

- Non Punch Through (NPT) Fast IGBT®
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	225
		$T_C = 80^\circ C$	150
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	450
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	700
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	400A@480V

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 500\mu A$	600			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$		1	500	μA
		$V_{CE} = 600V$		1		mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$	1.7	2.0	2.5	V
		$I_C = 200A$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4 mA$	4.5		6.5	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		9000		pF
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		800		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 1.5\Omega$		163		ns
T_r	Rise Time			43		
$T_{d(off)}$	Turn-off Delay Time			253		
T_f	Fall Time			33		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 1.5\Omega$		180		ns
T_r	Rise Time			49		
$T_{d(off)}$	Turn-off Delay Time			285		
T_f	Fall Time			41		
E_{off}	Turn off Energy			6.3		mJ

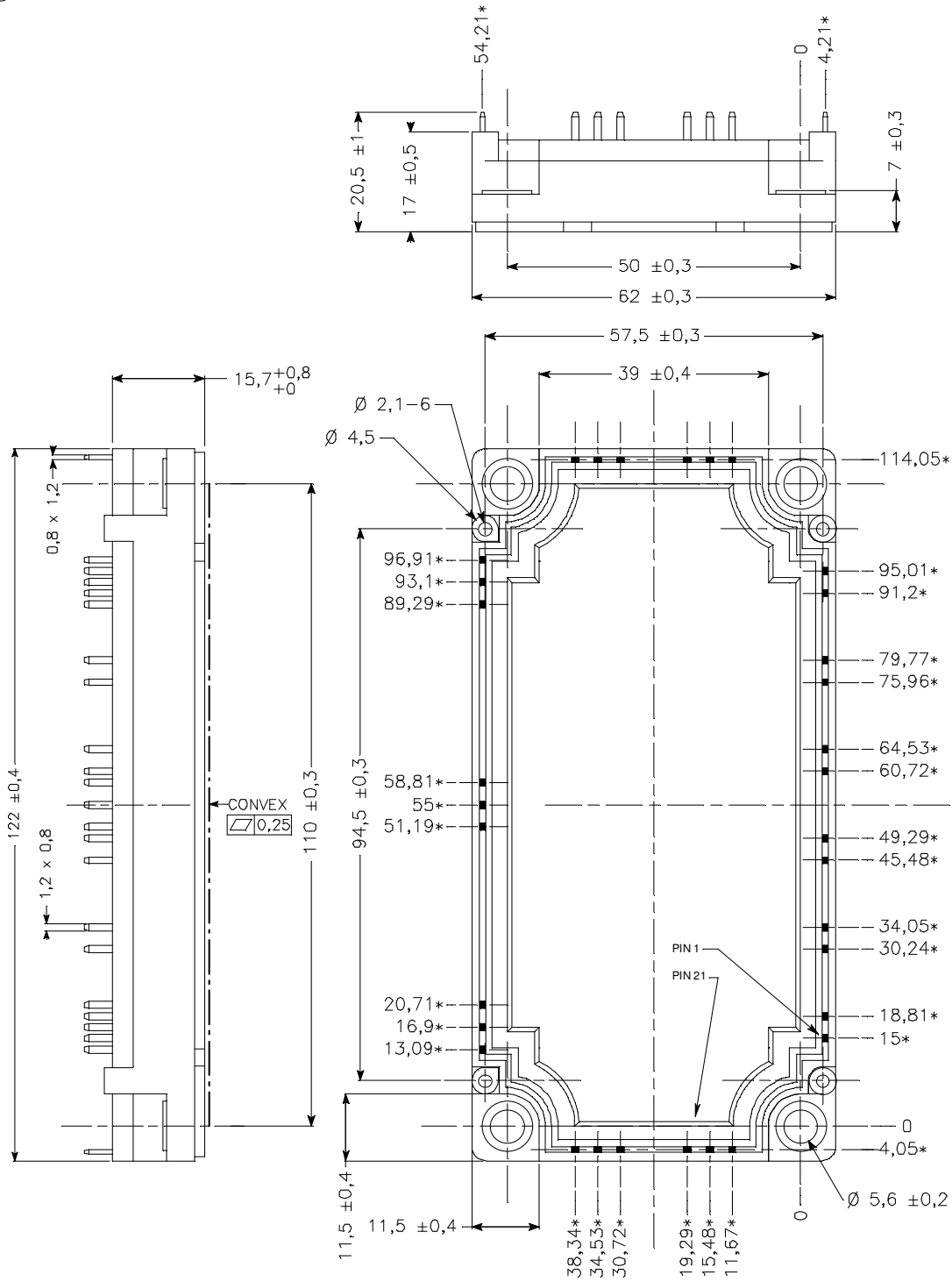
Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 200A$		1.25	1.6	V
		$V_{GE} = 0V$		1.2		
E_r	Reverse Recovery Energy	$I_F = 200A$ $V_R = 300V$ $di/dt = 800A/\mu s$		4.1		mJ
Q_{rr}	Reverse Recovery Charge	$I_F = 200A$		13		μC
		$V_R = 300V$ $di/dt = 800A/\mu s$		20		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case	IGBT		0.18	$^\circ\text{C/W}$	
		Diode		0.32		
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1 \text{ min}$, $I_{isol} < 1mA, 50/60Hz$	2500			V	
T_j	Operating junction temperature range	-40		150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		125		
Torque	Mounting torque	To heatsink	M5	3	4.5	N.m
Wt	Package Weight				300	g

Package outline



ALL DIMENSIONS MARKED "*" ARE TOLERENCED AS : $\oplus \varnothing 0,4$

APT reserves the right to change, without notice, the specifications and information contained herein

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